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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

| Details |
|---------|
|---------|

| Details | |
|--------------------------------|---|
| Product Status | Obsolete |
| Number of LABs/CLBs | - |
| Number of Logic Elements/Cells | - |
| Total RAM Bits | 55296 |
| Number of I/O | 194 |
| Number of Gates | 400000 |
| Voltage - Supply | 1.425V ~ 1.575V |
| Mounting Type | Surface Mount |
| Operating Temperature | 0°C ~ 85°C (TJ) |
| Package / Case | 484-BGA |
| Supplier Device Package | 484-FPBGA (23x23) |
| Purchase URL | https://www.e-xfl.com/product-detail/microsemi/a3p400-1fgg484 |
| | |

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



| ProASIC3 Devices | A3P015 ¹ | A3P030 | A3P060 | A3P125 | A3P250 | A3P400 | A3P600 | A3P1000 |
|--------------------------------|---------------------|-----------------------------------|-------------------------|--------------------|---------------------------------|----------------------------|----------------------------|----------------------------|
| Cortex-M1 Devices ² | | | | | M1A3P250 | M1A3P400 | M1A3P600 | M1A3P1000 |
| Package Pins QFN | QN68 | QN48, QN68, QN132 ⁷ | QN132 ⁷ | QN132 ⁷ | QN132 ⁷ | | | |
| CS VQFP TQFP | | VQ100 | CS121 VQ100 TQ144 | VQ100 TQ144 | VQ100 | | | |
| PQFP FBGA | | | FG144 | PQ208 FG144 | PQ208 FG144/256 ⁵ | PQ208 FG144/256/ 484 | PQ208 FG144/256/ 484 | PQ208 FG144/256/ 484 |

Notes:

- A3P015 is not recommended for new designs.
 Refer to the Cortex-M1 product brief for more information.
 AES is not available for Cortex-M1 ProASIC3 devices.
 Six chip (main) and three quadrant global networks are available for A3P060 and above.
 The M1A3P250 device does not support this package.
 For higher densities and support of additional features, refer to the ProASIC3E Flash Family FPGAs datasheet.
 Package not available.



Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3 device provides the best available security for programmable logic designs.

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system powerup (unlike SRAM-based FPGAs). Therefore, flash-based ProASIC3 FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based ProASIC3 devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based ProASIC3 devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs that are used for these purposes in a system. In addition, glitches and brownouts in system power will not corrupt the ProASIC3 device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based ProASIC3 devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of ProASIC3 flash-based FPGAs. Once it is programmed, the flash cell configuration element of ProASIC3 FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Low Power

Flash-based ProASIC3 devices exhibit power characteristics similar to an ASIC, making them an ideal choice for power-sensitive applications. ProASIC3 devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

ProASIC3 devices also have low dynamic power consumption to further maximize power savings.



The CCC block has these key features:

- Wide input frequency range (f_{IN CCC}) = 1.5 MHz to 350 MHz
- Output frequency range (f_{OUT CCC}) = 0.75 MHz to 350 MHz
- Clock delay adjustment via programmable and fixed delays from -7.56 ns to +11.12 ns
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time = 300 µs (for PLL only)
- Low power consumption of 5 mW
- Exceptional tolerance to input period jitter— allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × (350 MHz / f_{OUT_CCC}) (for PLL only)

Global Clocking

ProASIC3 devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high fanout nets.



0-I/O is set to drive out logic Low

Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

Z -Tristate: I/O is tristated

| om file Save to file | | | Show BSR De | |
|----------------------|-----------------------|------------|-------------------------|--|
| Port Name | Macro Cell | Pin Number | 1/O State (Output Only) | |
| BIST | ADLIB:INBUF | T2 | 1 | |
| BYPASS_IO | ADLIB:INBUF | K1 | 1 | |
| CLK | ADLIB:INBUF | B1 | 1 | |
| ENOUT | ADLIB:INBUF | J16 | 1 | |
| LED | ADLIB:OUTBUF | M3 | 0 | |
| MONITOR[0] | ADLIB:OUTBUF | B5 | 0 | |
| MONITOR[1] | ADLIB:OUTBUF | C7 | Z | |
| MONITOR[2] | ADLIB:OUTBUF | D9 | Z | |
| MONITOR[3] | ADLIB:OUTBUF | D7 | Z | |
| MONITOR[4] | ADLIB:OUTBUF | A11 | Z | |
| OEa | ADLIB:INBUF | E4 | Z | |
| ОЕЬ | ADLIB:INBUF | F1 | Z | |
| OSC_EN | ADLIB:INBUF | К3 | Z | |
| PAD(10) | ADLIB:BIBUF_LVCMOS33U | M8 | Z | |
| PAD[11] | ADLIB:BIBUF_LVCMOS33D | R7 | Z | |
| PAD[12] | ADLIB:BIBUF_LVCMOS33U | D11 | Z | |
| PAD[13] | ADLIB:BIBUF_LVCMOS33D | C12 | Z | |
| PAD[14] | ADLIB:BIBUF_LVCMOS33U | R6 | Z | |
| | | | | |

Figure 1-4 • I/O States During Programming Window

- 6. Click OK to return to the FlashPoint Programming File Generator window.
- Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.



F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

P_{AC1}, P_{AC2}, P_{AC3}, and P_{AC4} are device-dependent.

Sequential Cells Contribution—P_{S-CELL}

 $P_{S-CELL} = N_{S-CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$

 N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

 α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution—P_{C-CELL}

 $P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$

 $N_{C\mbox{-}C\mbox{-}E\mbox{-}L\mbox{-}L}$ is the number of VersaTiles used as combinatorial modules in the design.

 α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

 $\mathsf{F}_{\mathsf{CLK}}$ is the global clock signal frequency.

Routing Net Contribution—P_{NET}

 $P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

 α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

 F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution—PINPUTS

 $P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$

N_{INPUTS} is the number of I/O input buffers used in the design.

 α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-16 on page 2-14.

 F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution—POUTPUTS

 $P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$

N_{OUTPUTS} is the number of I/O output buffers used in the design.

 α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-16 on page 2-14.

 β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-17 on page 2-14.

F_{CLK} is the global clock signal frequency.



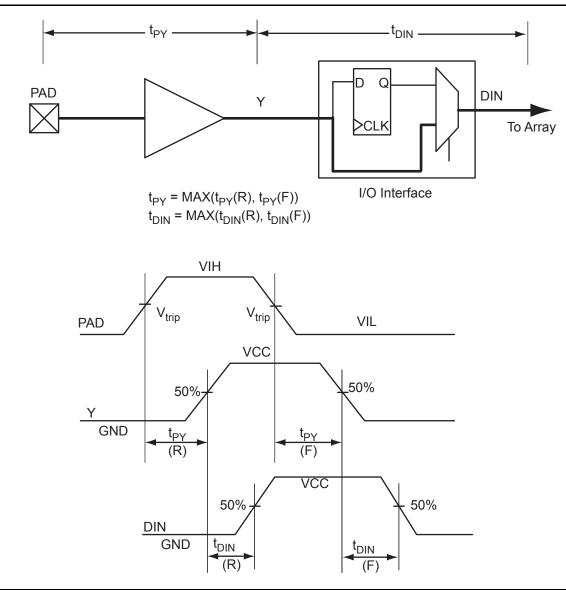


Figure 2-4 • Input Buffer Timing Model and Delays (Example)



Table 2-33 • I/O Short Currents IOSH/IOSL Applicable to Standard Plus I/O Banks

| | Drive Strength | IOSL (mA) ¹ | IOSH (mA) ¹ |
|--------------------------------------|--------------------------------|---------------------------------|---------------------------------|
| 3.3 V LVTTL / 3.3 V LVCMOS | 2 mA | 27 | 25 |
| | 4 mA | 27 | 25 |
| | 6 mA | 54 | 51 |
| | 8 mA | 54 | 51 |
| | 12 mA | 109 | 103 |
| | 16 mA | 109 | 103 |
| 3.3 V LVCMOS Wide Range ² | 100 µA | Same as regular 3.3 V LVCMOS | Same as regular 3.3 V LVCMOS |
| 2.5 V LVCMOS | 2 mA | 18 | 16 |
| | 4 mA | 18 | 16 |
| | 6 mA | 37 | 32 |
| | 8 mA | 37 | 32 |
| | 12 mA | 74 | 65 |
| 1.8 V LVCMOS | 2 mA | 11 | 9 |
| | 4 mA | 22 | 17 |
| | 6 mA | 44 | 35 |
| | 8 mA | 44 | 35 |
| 1.5 V LVCMOS | 2 mA | 16 | 13 |
| | 4 mA | 33 | 25 |
| 3.3 V PCI/PCI-X | Per PCI/PCI-X specification | 109 | 103 |

Notes:

1. $T_J = 100^{\circ}C$

 Applicable to 3.3 V LVCMOS Wide Range. IOSL/IOSH dependent on the I/O buffer drive strength selected for wide range applications. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.



| | Applicable to Standard Plus I/O Banks | | | | | | | | | | | | |
|-------------------|---------------------------------------|-------------------|-----------------|------------------|-----------------|-------------------|-----------------|-----------------|-----------------|-----------------|------------------|------------------|-------|
| Drive Strength | Speed Grade | t _{DOUT} | t _{DP} | t _{DIN} | t _{PY} | t _{EOUT} | t _{ZL} | t _{zH} | t _{LZ} | t _{HZ} | t _{ZLS} | t _{zHS} | Units |
| 2 mA | Std. | 0.66 | 9.68 | 0.04 | 1.00 | 0.43 | 9.86 | 8.42 | 2.28 | 2.21 | 12.09 | 10.66 | ns |
| | -1 | 0.56 | 8.23 | 0.04 | 0.85 | 0.36 | 8.39 | 7.17 | 1.94 | 1.88 | 10.29 | 9.07 | ns |
| | -2 | 0.49 | 7.23 | 0.03 | 0.75 | 0.32 | 7.36 | 6.29 | 1.70 | 1.65 | 9.03 | 7.96 | ns |
| 4 mA | Std. | 0.66 | 9.68 | 0.04 | 1.00 | 0.43 | 9.86 | 8.42 | 2.28 | 2.21 | 12.09 | 10.66 | ns |
| | -1 | 0.56 | 8.23 | 0.04 | 0.85 | 0.36 | 8.39 | 7.17 | 1.94 | 1.88 | 10.29 | 9.07 | ns |
| | -2 | 0.49 | 7.23 | 0.03 | 0.75 | 0.32 | 7.36 | 6.29 | 1.70 | 1.65 | 9.03 | 7.96 | ns |
| 6 mA | Std. | 0.66 | 6.70 | 0.04 | 1.00 | 0.43 | 6.82 | 5.89 | 2.58 | 2.74 | 9.06 | 8.12 | ns |
| | -1 | 0.56 | 5.70 | 0.04 | 0.85 | 0.36 | 5.80 | 5.01 | 2.20 | 2.33 | 7.71 | 6.91 | ns |
| | -2 | 0.49 | 5.00 | 0.03 | 0.75 | 0.32 | 5.10 | 4.40 | 1.93 | 2.05 | 6.76 | 6.06 | ns |
| 8 mA | Std. | 0.66 | 6.70 | 0.04 | 1.00 | 0.43 | 6.82 | 5.89 | 2.58 | 2.74 | 9.06 | 8.12 | ns |
| | -1 | 0.56 | 5.70 | 0.04 | 0.85 | 0.36 | 5.80 | 5.01 | 2.20 | 2.33 | 7.71 | 6.91 | ns |
| | -2 | 0.49 | 5.00 | 0.03 | 0.75 | 0.32 | 5.10 | 4.40 | 1.93 | 2.05 | 6.76 | 6.06 | ns |
| 12 mA | Std. | 0.66 | 5.05 | 0.04 | 1.00 | 0.43 | 5.14 | 4.51 | 2.79 | 3.08 | 7.38 | 6.75 | ns |
| | -1 | 0.56 | 4.29 | 0.04 | 0.85 | 0.36 | 4.37 | 3.84 | 2.38 | 2.62 | 6.28 | 5.74 | ns |
| | -2 | 0.49 | 3.77 | 0.03 | 0.75 | 0.32 | 3.84 | 3.37 | 2.09 | 2.30 | 5.51 | 5.04 | ns |
| 16 mA | Std. | 0.66 | 5.05 | 0.04 | 1.00 | 0.43 | 5.14 | 4.51 | 2.79 | 3.08 | 7.38 | 6.75 | ns |
| | -1 | 0.56 | 4.29 | 0.04 | 0.85 | 0.36 | 4.37 | 3.84 | 2.38 | 2.62 | 6.28 | 5.74 | ns |
| | -2 | 0.49 | 3.77 | 0.03 | 0.75 | 0.32 | 3.84 | 3.37 | 2.09 | 2.30 | 5.51 | 5.04 | ns |

Table 2-44 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Standard Plus I/O Banks

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-45 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Standard I/O Banks

| Drive Strength | Speed Grade | t _{DOUT} | t _{DP} | t _{DIN} | t _{PY} | t _{EOUT} | t _{ZL} | t _{zH} | t _{LZ} | t _{HZ} | Units |
|-------------------|----------------|-------------------|-----------------|------------------|-----------------|-------------------|-----------------|-----------------|-----------------|-----------------|-------|
| 2 mA | Std. | 0.66 | 7.07 | 0.04 | 1.00 | 0.43 | 7.20 | 6.23 | 2.07 | 2.15 | ns |
| | -1 | 0.56 | 6.01 | 0.04 | 0.85 | 0.36 | 6.12 | 5.30 | 1.76 | 1.83 | ns |
| | -2 | 0.49 | 5.28 | 0.03 | 0.75 | 0.32 | 5.37 | 4.65 | 1.55 | 1.60 | ns |
| 4 mA | Std. | 0.66 | 7.07 | 0.04 | 1.00 | 0.43 | 7.20 | 6.23 | 2.07 | 2.15 | ns |
| | –1 | 0.56 | 6.01 | 0.04 | 0.85 | 0.36 | 6.12 | 5.30 | 1.76 | 1.83 | ns |
| | -2 | 0.49 | 5.28 | 0.03 | 0.75 | 0.32 | 5.37 | 4.65 | 1.55 | 1.60 | ns |
| 6 mA | Std. | 0.66 | 4.41 | 0.04 | 1.00 | 0.43 | 4.49 | 3.75 | 2.39 | 2.69 | ns |
| | –1 | 0.56 | 3.75 | 0.04 | 0.85 | 0.36 | 3.82 | 3.19 | 2.04 | 2.29 | ns |
| | -2 | 0.49 | 3.29 | 0.03 | 0.75 | 0.32 | 3.36 | 2.80 | 1.79 | 2.01 | ns |
| 8 mA | Std. | 0.66 | 4.41 | 0.04 | 1.00 | 0.43 | 4.49 | 3.75 | 2.39 | 2.69 | ns |
| | -1 | 0.56 | 3.75 | 0.04 | 0.85 | 0.36 | 3.82 | 3.19 | 2.04 | 2.29 | ns |



2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

| 2.5 V LVCMOS | V | ΊL | V | ΊH | VOL | VOH | IOL | IOH | IOSL | IOSH | IIL1 | IIH ² |
|----------------|-----------|-----------|-----------|-----------|-----------|-----------|-----|-----|-------------------------|-------------------------|-----------------|------------------|
| Drive Strength | Min. V | Max. V | Min. V | Max. V | Max. V | Min. V | mA | mA | Max. mA ³ | Max. mA ³ | μA ⁴ | μA ⁴ |
| 2 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 2 | 2 | 18 | 16 | 10 | 10 |
| 4 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 4 | 4 | 18 | 16 | 10 | 10 |
| 6 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 6 | 6 | 37 | 32 | 10 | 10 |
| 8 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 8 | 8 | 37 | 32 | 10 | 10 |
| 12 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 12 | 12 | 74 | 65 | 10 | 10 |
| 16 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 16 | 16 | 87 | 83 | 10 | 10 |
| 24 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 24 | 24 | 124 | 169 | 10 | 10 |

Table 2-56 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.

Table 2-57 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

| 2.5 V LVCMOS | v | IL | v | IH | VOL | VOH | IOL | ЮН | IOSL | IOSH | IIL ¹ | IIH ² |
|----------------|-----------|-----------|-----------|-----------|-----------|-----------|-----|----|-------------------------|-------------------------|------------------|------------------|
| Drive Strength | Min. V | Max. V | Min. V | Max. V | Max. V | Min. V | mA | mA | Max. mA ³ | Max. mA ³ | μA ⁴ | μA ⁴ |
| 2 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 2 | 2 | 18 | 16 | 10 | 10 |
| 4 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 4 | 4 | 18 | 16 | 10 | 10 |
| 6 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 6 | 6 | 37 | 32 | 10 | 10 |
| 8 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 8 | 8 | 37 | 32 | 10 | 10 |
| 12 mA | -0.3 | 0.7 | 1.7 | 2.7 | 0.7 | 1.7 | 12 | 12 | 74 | 65 | 10 | 10 |

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

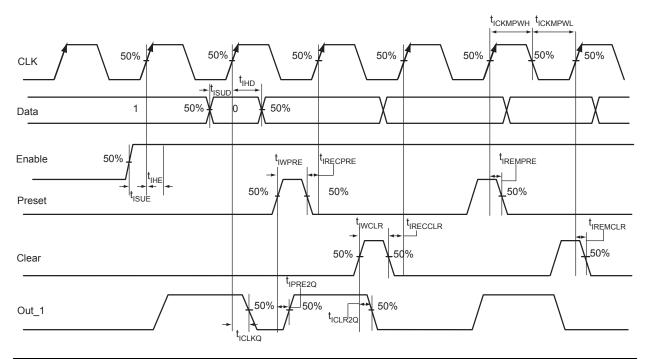
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

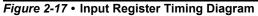
4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.



Input Register





Timing Characteristics

Table 2-98 • Input Data Register Propagation DelaysCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V

| Parameter | Description | -2 | -1 | Std. | Units |
|----------------------|---|------|------|------|-------|
| t _{ICLKQ} | Clock-to-Q of the Input Data Register | 0.24 | 0.27 | 0.32 | ns |
| t _{ISUD} | Data Setup Time for the Input Data Register | 0.26 | 0.30 | 0.35 | ns |
| t _{IHD} | Data Hold Time for the Input Data Register | 0.00 | 0.00 | 0.00 | ns |
| t _{ISUE} | Enable Setup Time for the Input Data Register | 0.37 | 0.42 | 0.50 | ns |
| t _{IHE} | Enable Hold Time for the Input Data Register | 0.00 | 0.00 | 0.00 | ns |
| t _{ICLR2Q} | Asynchronous Clear-to-Q of the Input Data Register | 0.45 | 0.52 | 0.61 | ns |
| t _{IPRE2Q} | Asynchronous Preset-to-Q of the Input Data Register | 0.45 | 0.52 | 0.61 | ns |
| t _{IREMCLR} | Asynchronous Clear Removal Time for the Input Data Register | 0.00 | 0.00 | 0.00 | ns |
| t _{IRECCLR} | Asynchronous Clear Recovery Time for the Input Data Register | 0.22 | 0.25 | 0.30 | ns |
| t _{IREMPRE} | Asynchronous Preset Removal Time for the Input Data Register | 0.00 | 0.00 | 0.00 | ns |
| t _{IRECPRE} | Asynchronous Preset Recovery Time for the Input Data Register | 0.22 | 0.25 | 0.30 | ns |
| t _{IWCLR} | Asynchronous Clear Minimum Pulse Width for the Input Data Register | 0.22 | 0.25 | 0.30 | ns |
| t _{IWPRE} | Asynchronous Preset Minimum Pulse Width for the Input Data Register | 0.22 | 0.25 | 0.30 | ns |
| t _{ICKMPWH} | Clock Minimum Pulse Width High for the Input Data Register | 0.36 | 0.41 | 0.48 | ns |
| t _{ICKMPWL} | Clock Minimum Pulse Width Low for the Input Data Register | 0.32 | 0.37 | 0.43 | ns |

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



Output Enable Register

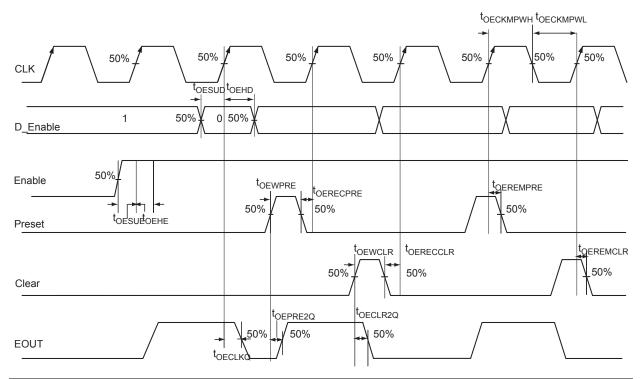


Figure 2-19 • Output Enable Register Timing Diagram



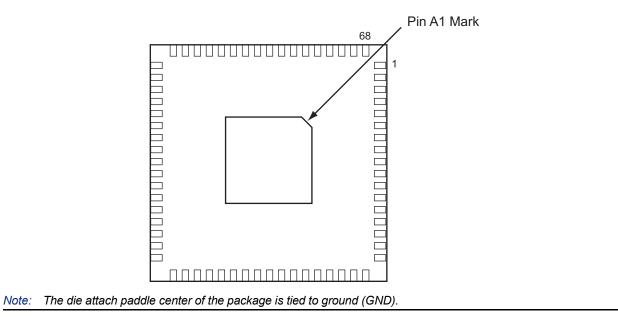
Table 2-120 • A3P250 FIFO 512×8

Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

| Parameter | Description | -2 | -1 | Std. | Units |
|----------------------|---|------|------|------|-------|
| t _{ENS} | REN, WEN Setup Time | 3.75 | 4.27 | 5.02 | ns |
| t _{ENH} | REN, WEN Hold Time | 0.00 | 0.00 | 0.00 | ns |
| t _{BKS} | BLK Setup Time | 0.19 | 0.22 | 0.26 | ns |
| t _{BKH} | BLK Hold Time | 0.00 | 0.00 | 0.00 | ns |
| t _{DS} | Input Data (WD) Setup Time | 0.18 | 0.21 | 0.25 | ns |
| t _{DH} | Input Data (WD) Hold Time | 0.00 | 0.00 | 0.00 | ns |
| t _{CKQ1} | Clock High to New Data Valid on RD (flow-through) | 2.17 | 2.47 | 2.90 | ns |
| t _{CKQ2} | Clock High to New Data Valid on RD (pipelined) | 0.94 | 1.07 | 1.26 | ns |
| t _{RCKEF} | RCLK High to Empty Flag Valid | 1.72 | 1.96 | 2.30 | ns |
| t _{WCKFF} | WCLK High to Full Flag Valid | 1.63 | 1.86 | 2.18 | ns |
| t _{CKAF} | Clock High to Almost Empty/Full Flag Valid | 6.19 | 7.05 | 8.29 | ns |
| t _{RSTFG} | RESET Low to Empty/Full Flag Valid | 1.69 | 1.93 | 2.27 | ns |
| t _{RSTAF} | RESET Low to Almost Empty/Full Flag Valid | 6.13 | 6.98 | 8.20 | ns |
| t _{RSTBQ} | RESET Low to Data Out Low on RD (flow-through) | 0.92 | 1.05 | 1.23 | ns |
| | RESET Low to Data Out Low on RD (pipelined) | 0.92 | 1.05 | 1.23 | ns |
| t _{REMRSTB} | RESET Removal | 0.29 | 0.33 | 0.38 | ns |
| t _{RECRSTB} | RESET Recovery | 1.50 | 1.71 | 2.01 | ns |
| t _{MPWRSTB} | RESET Minimum Pulse Width | 0.21 | 0.24 | 0.29 | ns |
| t _{CYC} | Clock Cycle Time | 3.23 | 3.68 | 4.32 | ns |
| F _{MAX} | Maximum Frequency for FIFO | 310 | 272 | 231 | MHz |



QN68 – Bottom View



Note

For more information on package drawings, see PD3068: Package Mechanical Drawings.



Package Pin Assignments

| QN132 | | | | | | | |
|------------|-----------------|--|--|--|--|--|--|
| Pin Number | A3P030 Function | | | | | | |
| C17 | IO51RSB1 | | | | | | |
| C18 | NC | | | | | | |
| C19 | ТСК | | | | | | |
| C20 | NC | | | | | | |
| C21 | VPUMP | | | | | | |
| C22 | VJTAG | | | | | | |
| C23 | NC | | | | | | |
| C24 | NC | | | | | | |
| C25 | NC | | | | | | |
| C26 | GDB0/IO38RSB0 | | | | | | |
| C27 | NC | | | | | | |
| C28 | VCCIB0 | | | | | | |
| C29 | IO32RSB0 | | | | | | |
| C30 | IO29RSB0 | | | | | | |
| C31 | IO28RSB0 | | | | | | |
| C32 | IO25RSB0 | | | | | | |
| C33 | NC | | | | | | |
| C34 | NC | | | | | | |
| C35 | VCCIB0 | | | | | | |
| C36 | IO17RSB0 | | | | | | |
| C37 | IO14RSB0 | | | | | | |
| C38 | IO11RSB0 | | | | | | |
| C39 | IO07RSB0 | | | | | | |
| C40 | IO04RSB0 | | | | | | |
| D1 | GND | | | | | | |
| D2 | GND | | | | | | |
| D3 | GND | | | | | | |
| D4 | GND | | | | | | |



Package Pin Assignments

| QN132 | | | | |
|----------------------------|---------------|--|--|--|
| Pin Number A3P060 Function | | | | |
| C17 | IO57RSB1 | | | |
| C18 | NC | | | |
| C19 | тск | | | |
| C20 | VMV1 | | | |
| C21 | VPUMP | | | |
| C22 | VJTAG | | | |
| C23 | VCCIB0 | | | |
| C24 | NC | | | |
| C25 | NC | | | |
| C26 | GCA1/IO42RSB0 | | | |
| C27 | GCC0/IO39RSB0 | | | |
| C28 | VCCIB0 | | | |
| C29 | IO29RSB0 | | | |
| C30 | GNDQ | | | |
| C31 | GBA1/IO27RSB0 | | | |
| C32 | GBB0/IO24RSB0 | | | |
| C33 | VCC | | | |
| C34 | IO19RSB0 | | | |
| C35 | IO16RSB0 | | | |
| C36 | IO13RSB0 | | | |
| C37 | GAC1/IO10RSB0 | | | |
| C38 | NC | | | |
| C39 | GAA0/IO05RSB0 | | | |
| C40 | VMV0 | | | |
| D1 | GND | | | |
| D2 | GND | | | |
| D3 | GND | | | |
| D4 | GND | | | |

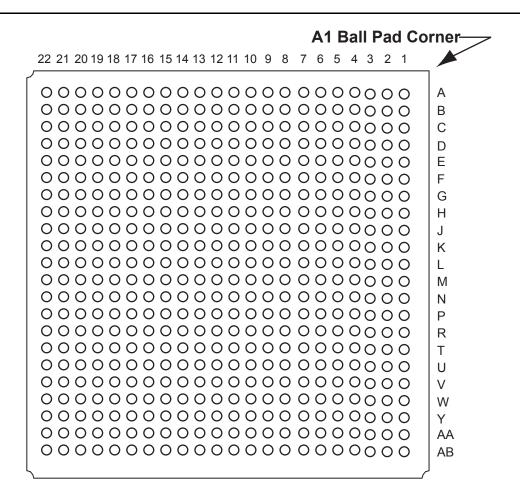


| CS121 | | | | |
|------------|-----------------|--|--|--|
| Pin Number | A3P060 Function | | | |
| K10 | VPUMP | | | |
| K11 | GDB1/IO47RSB0 | | | |
| L1 | VMV1 | | | |
| L2 | GNDQ | | | |
| L3 | IO65RSB1 | | | |
| L4 | IO63RSB1 | | | |
| L5 | IO61RSB1 | | | |
| L6 | IO58RSB1 | | | |
| L7 | IO57RSB1 | | | |
| L8 | IO55RSB1 | | | |
| L9 | GNDQ | | | |
| L10 | GDA0/IO50RSB0 | | | |
| L11 | VMV1 | | | |



| FG144 | | | | |
|------------|-----------------|--|--|--|
| Pin Number | A3P125 Function | | | |
| K1 | GEB0/IO109RSB1 | | | |
| K2 | GEA1/IO108RSB1 | | | |
| K3 | GEA0/IO107RSB1 | | | |
| K4 | GEA2/IO106RSB1 | | | |
| K5 | IO100RSB1 | | | |
| K6 | IO98RSB1 | | | |
| K7 | GND | | | |
| K8 | IO73RSB1 | | | |
| K9 | GDC2/IO72RSB1 | | | |
| K10 | GND | | | |
| K11 | GDA0/IO66RSB0 | | | |
| K12 | GDB0/IO64RSB0 | | | |
| L1 | GND | | | |
| L2 | VMV1 | | | |
| L3 | GEB2/IO105RSB1 | | | |
| L4 | IO102RSB1 | | | |
| L5 | VCCIB1 | | | |
| L6 | IO95RSB1 | | | |
| L7 | IO85RSB1 | | | |
| L8 | IO74RSB1 | | | |
| L9 | TMS | | | |
| L10 | VJTAG | | | |
| L11 | VMV1 | | | |
| L12 | TRST | | | |
| M1 | GNDQ | | | |
| M2 | GEC2/IO104RSB1 | | | |
| M3 | IO103RSB1 | | | |
| M4 | IO101RSB1 | | | |
| M5 | IO97RSB1 | | | |
| M6 | IO94RSB1 | | | |
| M7 | IO86RSB1 | | | |
| M8 | IO75RSB1 | | | |
| M9 | TDI | | | |
| M10 | VCCIB1 | | | |
| M11 | VPUMP | | | |
| M12 | M12 GNDQ | | | |

FG484 – Bottom View



Note

For more information on package drawings, see PD3068: Package Mechanical Drawings.



| | FG484 | FG484 | | | FG484 | |
|------------|-----------------|------------|-----------------|------------|-----------------|--|
| Pin Number | A3P400 Function | Pin Number | A3P400 Function | Pin Number | A3P400 Function | |
| E21 | NC | G13 | IO40RSB0 | J5 | IO149NPB3 | |
| E22 | NC | G14 | IO46RSB0 | J6 | IO09RSB0 | |
| F1 | NC | G15 | GNDQ | J7 | IO152UDB3 | |
| F2 | NC | G16 | IO47RSB0 | J8 | VCCIB3 | |
| F3 | NC | G17 | GBB2/IO61PPB1 | J9 | GND | |
| F4 | IO154VDB3 | G18 | IO53RSB0 | J10 | VCC | |
| F5 | IO155VDB3 | G19 | IO63NDB1 | J11 | VCC | |
| F6 | IO11RSB0 | G20 | NC | J12 | VCC | |
| F7 | IO07RSB0 | G21 | NC | J13 | VCC | |
| F8 | GAC0/IO04RSB0 | G22 | NC | J14 | GND | |
| F9 | GAC1/IO05RSB0 | H1 | NC | J15 | VCCIB1 | |
| F10 | IO20RSB0 | H2 | NC | J16 | IO62NDB1 | |
| F11 | IO24RSB0 | H3 | VCC | J17 | IO49RSB0 | |
| F12 | IO33RSB0 | H4 | IO150PDB3 | J18 | IO64PPB1 | |
| F13 | IO39RSB0 | H5 | IO08RSB0 | J19 | IO66NDB1 | |
| F14 | IO45RSB0 | H6 | IO153VDB3 | J20 | NC | |
| F15 | GBC0/IO54RSB0 | H7 | IO152VDB3 | J21 | NC | |
| F16 | IO48RSB0 | H8 | VMV0 | J22 | NC | |
| F17 | VMV0 | H9 | VCCIB0 | K1 | NC | |
| F18 | IO61NPB1 | H10 | VCCIB0 | K2 | NC | |
| F19 | IO63PDB1 | H11 | IO25RSB0 | K3 | NC | |
| F20 | NC | H12 | IO31RSB0 | K4 | IO148NDB3 | |
| F21 | NC | H13 | VCCIB0 | K5 | IO148PDB3 | |
| F22 | NC | H14 | VCCIB0 | K6 | IO149PPB3 | |
| G1 | NC | H15 | VMV1 | K7 | GFC1/IO147PPB3 | |
| G2 | NC | H16 | GBC2/IO62PDB1 | K8 | VCCIB3 | |
| G3 | NC | H17 | IO65RSB1 | K9 | VCC | |
| G4 | IO151VDB3 | H18 | IO52RSB0 | K10 | GND | |
| G5 | IO151UDB3 | H19 | IO66PDB1 | K11 | GND | |
| G6 | GAC2/IO153UDB3 | H20 | VCC | K12 | GND | |
| G7 | IO06RSB0 | H21 | NC | K13 | GND | |
| G8 | GNDQ | H22 | NC | K14 | VCC | |
| G9 | IO10RSB0 | J1 | NC | K15 | VCCIB1 | |
| G10 | IO19RSB0 | J2 | NC | K16 | GCC1/IO67PPB1 | |
| G11 | IO26RSB0 | J3 | NC | K17 | IO64NPB1 | |
| G12 | IO30RSB0 | J4 | IO150NDB3 | K18 | IO73PDB1 | |



5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each version of the ProASIC3 datasheet.

| Revision | Changes | Page |
|--------------------------------|---|---------------------------|
| Revision 18 (March 2016) | Updated 3.3 V DC supply voltage's maximum Commercial and Industrial values from 3.3 V to 3.6 V in Table 2-2 (SAR 72693). | |
| | Added reference of Package Mechanical Drawings document in all package pin assignment notes (76833). | NA |
| Revision 17 | Removed PQFP embedded heat spreader info. from Table 2-5 (SAR 52320). | 2-6 |
| (June 2015) | Updated "VCCIBx I/O Supply Voltage" (SAR 43323). | 3-1 |
| Revision 16 (December 2014) | Updated "ProASIC3 Ordering Information". Interchanged the positions of Y- Security Feature and I- Application (Temperature Range) (SAR 61079). Added Note "Only devices with package size greater than or equal to 5x5 are supported". | |
| | Updated Table Note (2) in Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature so that the Table Note is not applicable for Maximum Storage Temperature T_{STG} (SAR 54297). | |
| | Added values for Drive strength 2 mA in Table 2-41 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew, Table 2-42 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew, Table 2-43 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew, and Table 2-44 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew (SAR 57184). | 2-34, 2-35, 2-36, 2-37 |
| | Added Figure 2-1 • High-Temperature Data Retention (HTR) (SAR 45466). | 2-3 |
| | Updates made to maintain the style and consistency of the document. | NA |
| Revision 15 (July 2014) | Added corner pad table note (3) to "QN132 – Bottom View" (SAR 47442). | 4-6 |
| | Ambient temperature removed in Table 2-2, table notes and "ProASIC3 Ordering Information" figure were modified (SAR 48343). | 2-2 1-IV |
| | Other updates were made to maintain the style and consistency of the datasheet. | NA |
| Revision 14 (April 2014) | Note added for the discontinuance of QN132 package to the following tables and section: "ProASIC3 Devices", "I/Os Per Package 1", "ProASIC3 FPGAs Package Sizes Dimensions" and "QN132 – Bottom View" section (SAR 55118). | I, III, 4-6 |